Midium Power Transistors (50V / 4A)

2SCR543D

● Structure

NPN Silicon epitaxial planar transistor

● Features

1) Low saturation voltage

$V_{CE\ (sat)}$ = 0.35V (Max.) (I_C / I_B= 2A / 100mA)

2) High speed switching

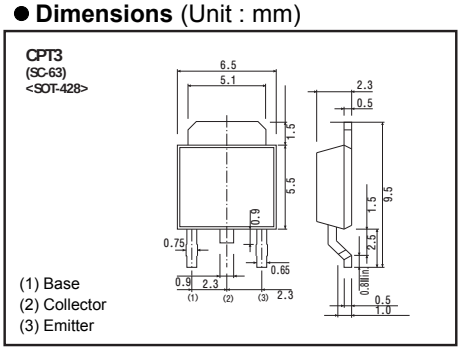
● Applications

Driver

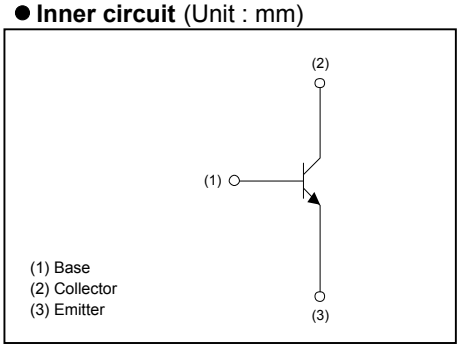
● Packaging specifications

Type	Package	CPT3
	Code	TL
	Basic ordering unit (pieces)	2500

● Dimensions (Unit : mm)



● Inner circuit (Unit : mm)



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	50	V
Collector-emitter voltage		V_{CEO}	50	V
Emitter-base voltage		V_{EBO}	6	V
Collector current	DC	I_C	4	A
	Pulsed	I_{CP} *1	8	A
Power dissipation		P_D *2	1	W
		P_D *3	10	W
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	-55 to 150	°C

*1 Pw=10ms, Single Pulse

*2 Mounted on a substrate

*3 T_C=25°C

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	50	-	-	V	I_C= 1mA
Collector-base breakdown voltage	BV_{CBO}	50	-	-	V	I_C= 100μA
Emitter-base breakdown voltage	BV_{EBO}	6	-	-	V	I_E= 100μA
Collector cut-off current	I_{CBO}	-	-	1	μA	V_{CB}= 50V
Emitter cut-off current	I_{EBO}	-	-	1	μA	V_{EB}= 4V
Collector-emitter staturation voltage	$V_{CE(sat)}$ *1	-	130	350	mV	I_C= 2A, I_B= 100mA
DC current gain	h_{FE}	180	-	450	-	V_{CE}= 3V, I_C= 100mA
Transition frequency	f_T *1	-	300	-	MHz	V_{CE}= 10V I_E=-500mA, f=100MHz
Collector output capacitance	C_{ob}	-	20	-	pF	V_{CB}= 10V, I_E=0A f=1MHz
Turn-on time	t_{on} *2	-	50	-	ns	I_C= 2A, I_{B1}= 200mA, I_{B2}=-200mA, V_{CC}≃10V
Storage time	t_{stg} *2	-	450	-	ns	
Fall time	t_f *2	-	85	-	ns	

*1 Pulsed

*2 See switching time test circuit

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical OutputCharacteristics

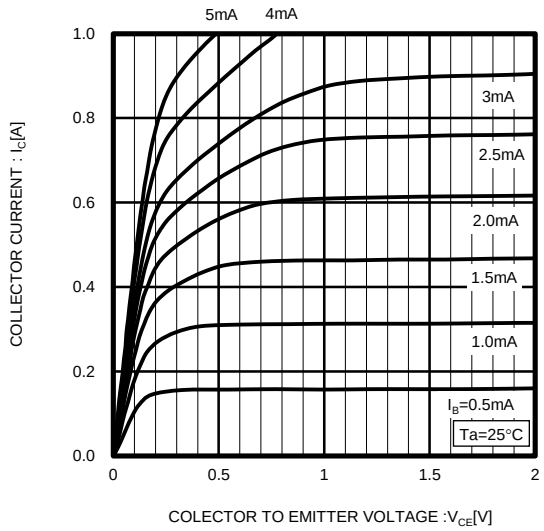


Fig.2 DC Current Gain vs. Collector Current (I)

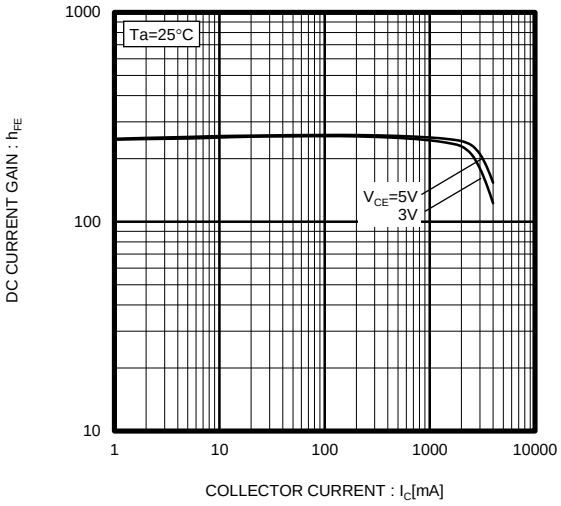


Fig3. DC Current Gain vs. Collector Current (II)

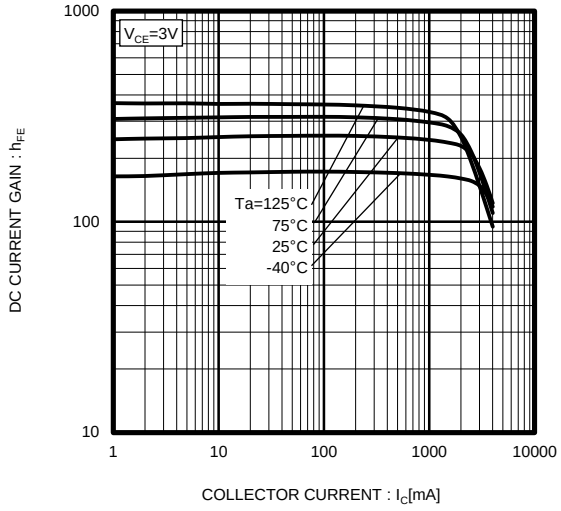


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (I)

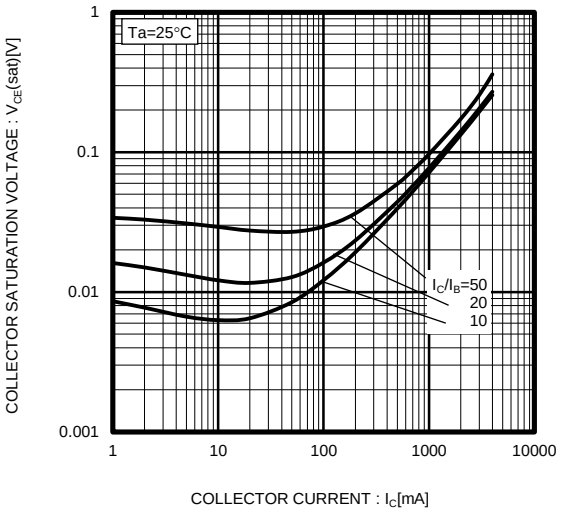


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (II)

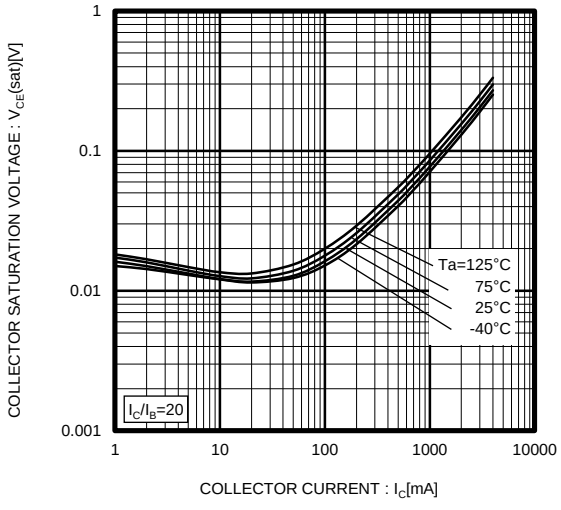


Fig.6 Ground Emitter Propagation Characteristics

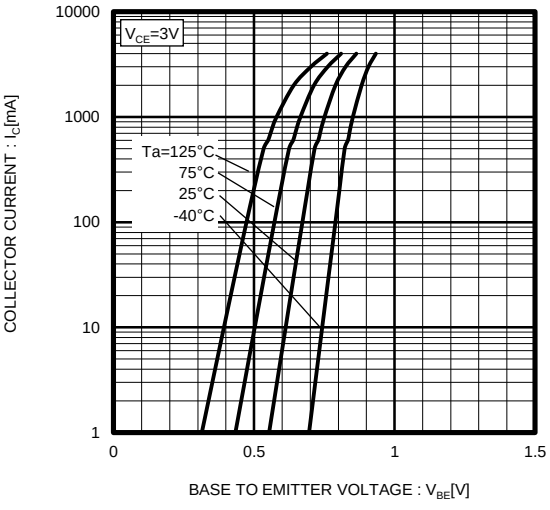


Fig.7 Emitter Input Capacitance vs. Emitter-Base Voltage
Collector Output Capacitance vs. Collector-Base Voltage

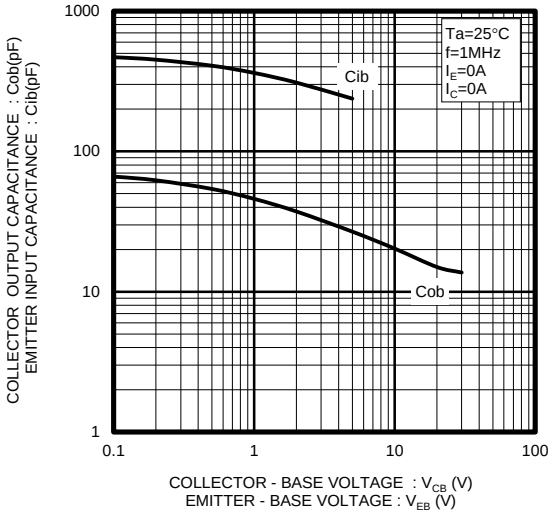


Fig.8 Gain Bandwidth Product vs. Emitter Current

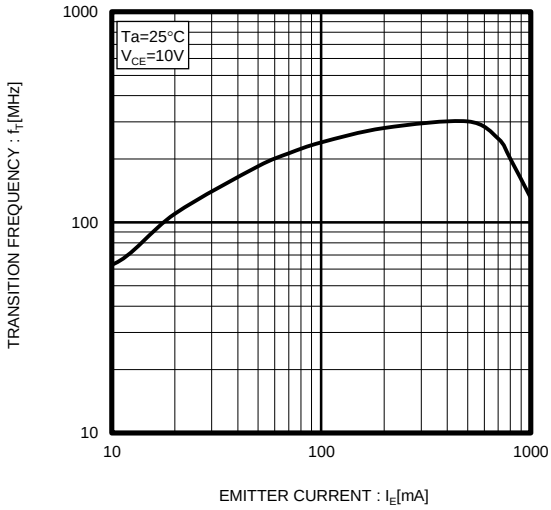
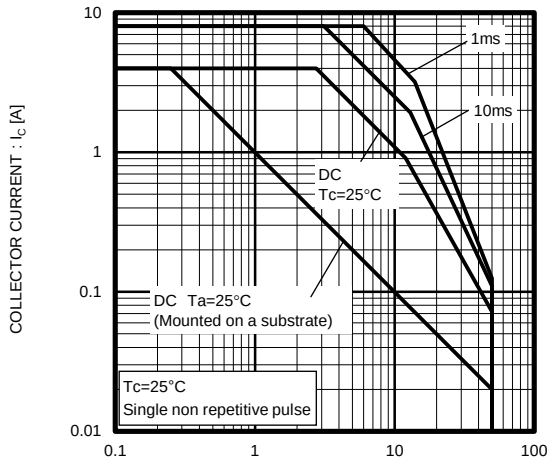
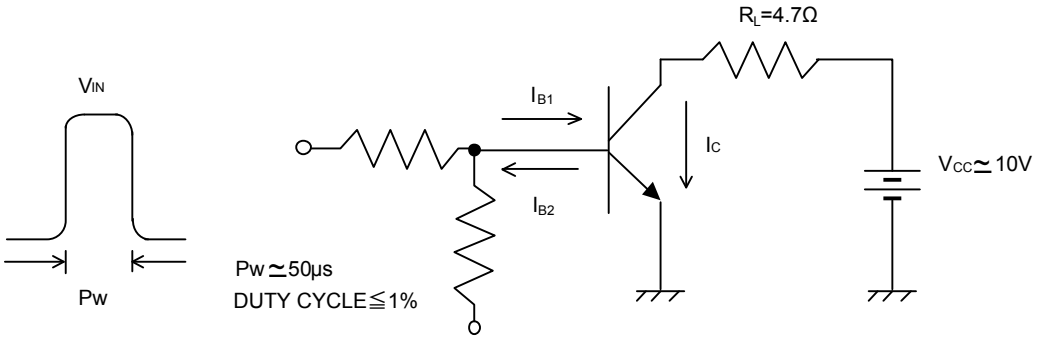


Fig.9 Safe Operating Area

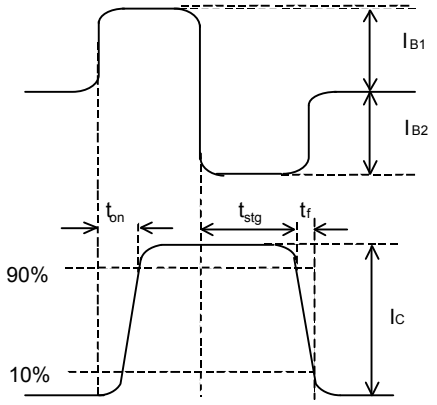


● **Switching time test circuit**



BASE CURENT WAVEFORM

COLLECTOR CURRENT WAVEFORM



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